



INFORMATION DISCLOSURE CITATION

OMB No. 0651-0011

Atty. Docket No.	04293101-01	Div. of Appln. No.	1 0/627,648
Applicant	Koji USUDA, et al.		
Filing Date	August 9, 2004	Prior Group:	2814

U.S. PATENT DOCUMENTS

Examiner Initial*	Document Number	Issue Date	Name	Class	Sub Class	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS

	Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No
PC	2003-234472	08/2003	Japan	/	/	No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Examiner	PHAT X. CAO	Date Considered	4/29/05
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Atty. Docket No.	04329.3101-01:	Div. of Appln. No.	1 0/627,648
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PC	McKee et al. "PHYSICAL STRUCTURE AND INVERSION CHARGE AT A SEMICONDUCTOR INTERFACE WITH A CRYSTALLINE OXIDE", Science, Vol. 293, pages 468-471, (2001)
PC	Nishikawa et al., "DIRECT GROWTH OF SINGLE CRYSTALLINE CeO ₂ HIGH-K GATE DIELECTRICS", Extended Abstracts of the 2001 International Conference on Solid State Devices and Materials, pages 174-175, (2001)
PC	Gottschalk et al., "EPITAXIAL Pr ₂ O ₃ ON SILICON AS AN ALTERNATIVE GATE OXIDE FOR FUTURE CMOS APPLICATIONS", JOINT SESSION CRYSTALLINE OXIDES FOR GATE DIELECTRICS, Session N8.5/T6.5, pages 350-351, (2002)
PC	Tezuka et al., "NOVEL FULLY-DEPLETED SiGe-ON-INSULATOR pMOSFETs WITH HIGH-MOBILITY SiGe SURFACE CHANNELS", IEDM Tech. Dig., 946, IEEE, (2001)
PC	Welser et al.; "STRAIN DEPENDENCE OF THE PERFORMANCE ENHANCEMENT IN STRAINED-Si n-MOSFETs"; IEDM, pages, 373-376, IEEE, (1994)
PC	Hirose et al.; "FUNDAMENTAL LIMIT OF GATE OXIDE THICKNESS SCALING IN ADVANCED MOSFETs"; Semicond. Sci. Technol. Vol. 15, pages 485-490, (2000)

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